

# 2SB1574 (Tentative)

Silicon PNP epitaxial planar type

For low-frequency output amplification

## Features

- Possible to solder radiation fin directly to printed circuit board
- Type with universal characteristics
- Collector breakdown voltage:  $V_{CBO}/V_{CEO} = -50V$
- Collector current:  $I_C = -2A$

## Absolute Maximum Ratings ( $T_C=25^\circ C$ )

Parameter	Symbol	Rated	Unit
Collector to base voltage	$V_{CBO}$	-50	V
Collector to emitter voltage	$V_{CEO}$	-50	V
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-3	A
Collector current	$I_C$	-2	A
Collector power dissipation ( $T_C=25^\circ C$ )	$P_C$	10	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

## Electrical Characteristics ( $T_C=25^\circ C$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -10V, I_E = 0$			-0.1	$\mu A$
Collector to base voltage	$V_{CBO}$	$I_C = -10\mu A, I_E = 0$	-50			V
Collector to emitter voltage	$V_{CEO}$	$I_C = -1mA, I_B = 0$	-50			V
Emitter to base voltage	$V_{EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE1}^*$	$V_{CE} = -2V, I_C = -200mA$	120		340	
	$h_{FE2}$	$V_{CE} = -2V, I_C = -1A$	60			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.2	-0.3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.85	-1.2	V
Transition frequency	$f_T$	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		80		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		45	60	pF

\* $h_{FE1}$  Rank classification

Rank	R	S
$h_{FE1}$	120 to 240	170 to 340

